BAS19L, BAS20L, BAS21L, BAS21DW5

High Voltage Switching Diode

Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage BAS19 BAS20 BAS21	V _R	120 200 250	Vdc
Repetitive Peak Reverse Voltage BAS19 BAS20 BAS21	V_{RRM}	120 200 250	Vdc
Continuous Forward Current	Ι _F	200	mAdc
Peak Forward Surge Current (1/2 Cycle, Sine Wave, 60 Hz)	I _{FSM}	2	Α
Repetitive Peak Forward Current (Pulse Train: T _{ON} = 1 s, T _{OFF} = 0.5 s)	I _{FRM}	0.6	А
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Power Dissipation (Note 1)	P _D	385	mW
Electrostatic Discharge	ESD	HM < 500	V
		MM < 400	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

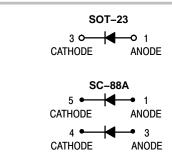
1. Mounted on FR-5 Board = 1.0 x 0.75 x 0.062 in.



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HIGH VOLTAGE SWITCHING DIODE



MARKING DIAGRAMS



SOT-23 (TO-236) CASE 318 STYLE 8





SC-88A (SOT-353) CASE 419A



x = P, R, or S P = BAS19LR = BAS20L

S = BAS21L or BAS21DW5

M = Date Code ■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon the manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

BAS19L, BAS20L, BAS21L, BAS21DW5

THERMAL CHARACTERISTICS (SOT-23)

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board	P _D	225	mW
(Note 2) T _A = 25°C Derate above 25°C		1.8	mW/°C
Thermal Resistance Junction-to-Ambient (SOT-23)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 3)	P _D	300	mW
T _A = 25°C Derate above 25°C		2.4	mW/°C
Thermal Resistance Junction–to–Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (SC-88A)

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 4)	P _D	385	mW
Thermal Resistance – Junction–to–Ambient Derate Above 25°C	$R_{ heta JA}$	328 3.0	°C/W mW/°C
Maximum Junction Temperature	T _{Jmax}	150	°C
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

^{2.} FR-5 = $1.0 \times 0.75 \times 0.062$ in.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

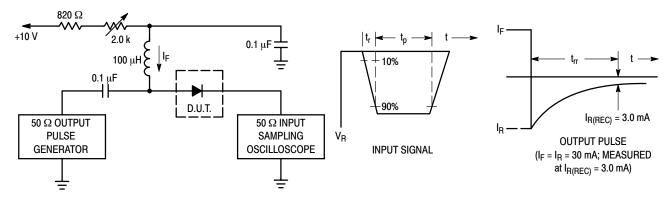
Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current	I _R			μAdc
(V _R = 100 Vdc) BAS19		_	0.1	
$(V_R = 150 \text{ Vdc})$ BAS20		_	0.1	
$(V_R = 200 \text{ Vdc})$ BAS21		_	0.1	
$(V_R = 100 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ BAS19		_	100	
$(V_R = 150 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ BAS20		_	100	
$(V_R = 200 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ BAS21		_	100	
Reverse Breakdown Voltage	V _(BR)			Vdc
(I _{BR} = 100 μAdc) BAS19		120	_	
$(I_{BR} = 100 \mu\text{Adc})$ BAS20		200	_	
(I _{BR} = 100 μAdc) BAS21		250	_	
Forward Voltage	V _F			Vdc
(I _F = 100 mAdc)		_	1.0	
(I _F = 200 mAdc)		_	1.25	
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	-	5.0	pF
Reverse Recovery Time ($I_F = I_R = 30 \text{ mAdc}$, $I_{R(REC)} = 3.0 \text{ mAdc}$, $R_L = 100$)	t _{rr}	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{3.} Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

^{4.} Mounted on FR-5 Board = $1.0 \times 0.75 \times 0.062$ in.

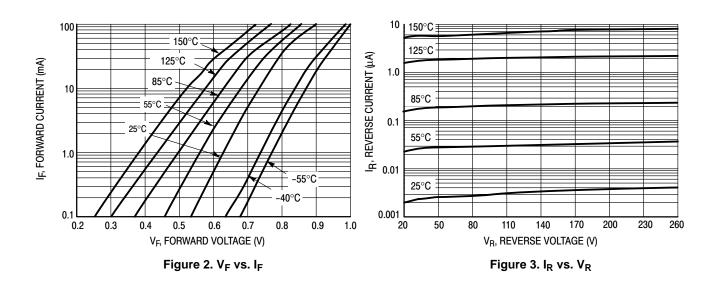
BAS19L, BAS20L, BAS21L, BAS21DW5



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA.

- 2. Input pulse is adjusted so I_{R(peak)} is equal to 30 mA.
- 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit



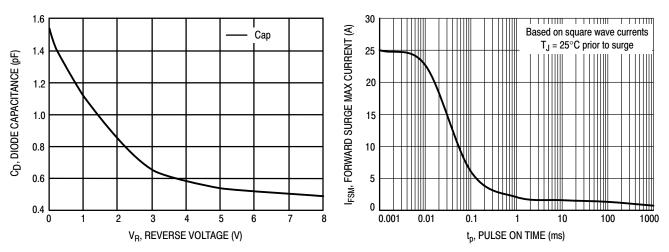


Figure 4. Capacitance

Figure 5. Forward Surge Current

BAS19L, BAS20L, BAS21L, BAS21DW5

ORDERING INFORMATION

Device	Package	Shipping [†]
BAS19LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS19LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
NSVBAS19LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS20LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS20LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
NSVBAS20LT3G*	SOT-23 (Pb-Free)	10000 / Tape & Reel
SBAS20LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS21LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SBAS21LT1G*	SOT-23 (Pb-Free)	3000 / Tape & Reel
BAS21LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
SBAS21LT3G*	SOT-23 (Pb-Free)	10000 / Tape & Reel
BAS21DW5T1G	SC-88A (Pb-Free)	3000 / Tape & Reel
SBAS21DW5T1G*	SC-88A (Pb-Free)	3000 / Tape & Reel
SBAS21DW5T3G*	SC-88A (Pb-Free)	10000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified

and PPAP Capable.



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

PROT	RUSIONS, OR GATE BURRS.	
		T

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	ANODE	CATHODE	ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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DESCRIPTION:

PAGE 1 OF 1



SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE L**

DATE 17 JAN 2013



- TIES:
 DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 419A-01 OBSOLETE. NEW STANDARD 3.
- 419A-02.
 DIMENSIONS A AND B DO NOT INCLUDE
- MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

-B-S D 5 PL 0.2 (0.008) M B M **SOLDER FOOTPRINT**

+++			
0.40			0.65 0.025
	<u>1.9</u> 0.0748	SCALE 20:1	$\left(\frac{\text{mm}}{\text{inches}}\right)$
OT # F 4	07450	07.45.0	

0.50 0.0197

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE 1	PIN 1. SOURCE 1	PIN 1. CATHODE
2. EMITTER	2. EMITTER	2. N/C	2. DRAIN 1/2	2. COMMON ANODE
3. BASE	3. BASE	3. ANODE 2	3. SOURCE 1	3. CATHODE 2
4. COLLECTOR	4. COLLECTOR	4. CATHODE 2	4. GATE 1	4. CATHODE 3
4. COLLECTOR	4. COLLECTOR	4. CATHODE 2	4. GATE 1	4. CATHODE 3
5. COLLECTOR	5. CATHODE	5. CATHODE 1	5. GATE 2	5. CATHODE 4

J. GOLLLOTON	3. CATTODE	J. CATHODE I	J. GAIL 2	J. CATTODE 4
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE 1	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DESCRIPTION:	SC-88A (SC-70-5/SOT-353)		PAGE 1 OF 1	

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